

PROCEEDINGS OF SPIE

# ***Alternative Lithographic Technologies V***

**William M. Tong**  
**Douglas J. Resnick**  
*Editors*

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**Christopher Bencher**, Applied Materials, Inc. (United States)

UV Imprint Lithography  
**Douglas J. Resnick**, Molecular Imprints, Inc. (United States)  
**Tatsuhiko Higashiki**, Toshiba Corporation (Japan)

DSA Materials and Processing: Joint Session with Conference 8680  
and 8682  
**Joy Y. Cheng**, IBM Almaden Research Center (United States)  
**Ralph R. Dammel**, AZ Electronic Materials USA Corporation  
(United States)

E-Beam Direct-Write for High-Volume Manufacturing I  
**Alan Brodie**, KLA-Tencor Corporation (United States)  
**Marco Wieland**, MAPPER Lithography (Netherlands)

Panel Discussion on Challenges for Directed Self-Assembly  
**William M. Tong**, KLA-Tencor Corporation (United States)  
**Joy Y. Cheng**, IBM Almaden Research Center (United States)

DSA Metrology and Inspection: Joint Session with Conferences 8680  
and 8681  
**Joy Y. Cheng**, IBM Almaden Research Center (United States)  
**Martha I. Sanchez**, IBM Almaden Research Center (United States)

E-Beam Direct-Write for High-Volume Manufacturing II  
**Shy-Jay Lin**, Taiwan Semiconductor Manufacturing Company Ltd.  
(Taiwan)  
**Hans Loeschner**, IMS Nanofabrication AG (Austria)

Nanoimprint Applications  
**Elizabeth A. Dobisz**, HGST (United States)  
**John G. Maltabes**, Hewlett-Packard Laboratories (United States)

Design for Manufacturability for DSA: Joint Session with Conferences  
8680 and 8684

**Benjamin M. Rathsack**, Tokyo Electron America, Inc. (United States)

**Lars W. Liebmann**, IBM Corporation (United States)

DSA Vias

**James Watkins**, University of Massachusetts Amherst (United States)

**Benjamin M. Rathsack**, Tokyo Electron America, Inc. (United States)

Nanoprobe Array Direct-Write Technologies

**Ivo W. Rangelow**, Technische Universität Ilmenau (Germany)

**Frank M. Schellenberg**, Consultant (United States)

E-Beam Direct-Write for High-Volume Manufacturing III

**Ines A. Stolberg**, Vistec Electron Beam Lithography Group (Germany)

**Marco Wieland**, MAPPER Lithography (Netherlands)

DSA Lines-Spaces

**Frank M. Schellenberg**, Consultant (United States)

**Christopher Bencher**, Applied Materials, Inc. (United States)

